

描述 / Descriptions

TOLL-8L 封装 N 沟道场效应管。

N-Channel MOSFET in a TOLL-8L Plastic Package .

特征 / Features

$V_{DS}(V)=100V$ $I_D=259A$

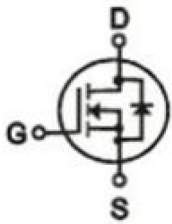
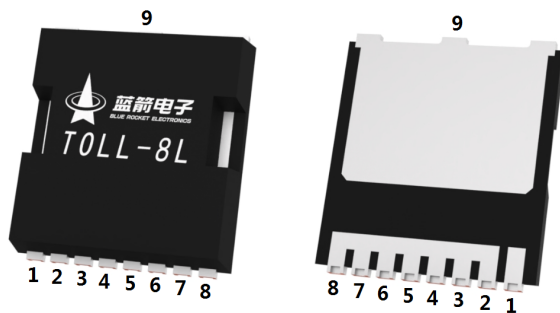
$R_{DS(ON)}@10V \leq 2.0m\Omega$ (Typ. $1.6m\Omega$)

无卤产品。 HF Product.

用途 / Applications

DC/DC 转换器、电源开关、电机驱动。

DC/DC converter, Power switch, Motor drives.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN1: G PIN2、3、4、5、6、7、8: S PIN9: D

印章代码 / Marking

见印章说明。

See Marking Instructions.

极限参数 / Absolute Maximum Ratings($T_c=25^\circ\text{C}$)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V_{DS}	100	V
Drain Current - Continuous		I_D	259	A
Drain Current – Pulsed		I_{DM}	1036	A
Gate-Source Voltage		V_{GS}	± 20	V
Power Dissipation		P_{tot}	250	W
Single Pulse Avalanche Energy($V_{DD}=50\text{V}, L=0.1\text{mH}$)		E_{AS}	205	mJ
Junction and Storage Temperature Range		T_j, T_{stg}	-55 to 150	$^\circ\text{C}$
Thermal resistance, junction - ambient	Steady-State	$R_{\theta JA}$	40	$^\circ\text{C}/\text{W}$
Thermal resistance, junction - case	Steady-State	$R_{\theta JC}$	0.5	

电性能参数 / Electrical Characteristics($T_a=25^\circ\text{C}$)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100\text{V}, V_{GS}=0\text{V}$			1	μA
Gate-Body leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	2.2	3.0	3.8	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}, I_D=100\text{A}$		1.6	2.0	$\text{m}\Omega$
Diode Forward Voltage	V_{SD}	$I_S=100\text{A}, V_{GS}=0\text{V}$		0.9	1.2	V
Gate Resistance	R_g	$f=1.0\text{MHz}$		1.2		Ω
Input Capacitance	C_{iss}	$V_{DS}=50\text{V}, V_{GS}=0\text{V}, f=1.0\text{MHz}$		10120		pF
Output Capacitance	C_{oss}			1360		
Reverse Transfer Capacitance	C_{rss}			50		
Total Gate Charge	Q_g	$V_{GS}=10\text{V}, I_{DS}=100\text{A}, V_{DS}=50\text{V}$		176		nC
Gate Source Charge	Q_{gs}			47		
Gate Drain Charge	Q_{gd}			54		

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=50V$ $R_G=6\ \Omega$ $I_D=100A$		85		ns
Turn-On Rise Time	t_r			137		
Turn-Off Delay Time	$t_{d(off)}$			92		
Turn-Off Fall Time	t_f			98		
Reverse Recovery Time	t_{rr}	$I_F = 50\ A, V_{DS} = 50\ V$ $di_{SD}/dt = 100\ A/\mu s$		79		ns
Reverse Recovery Charge	Q_{rr}			180		nC

电参数曲线图 / Electrical Characteristic Curve

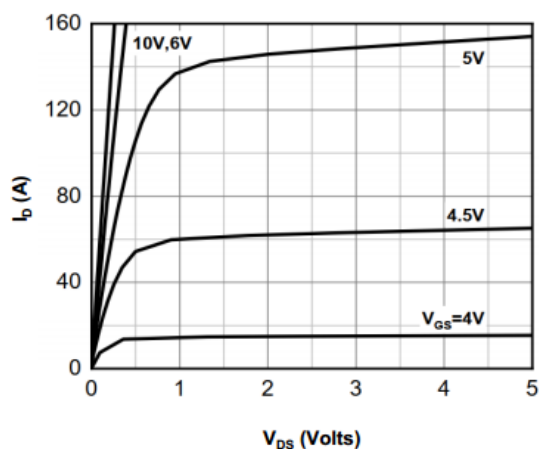


Figure 1: On-Region Characteristics

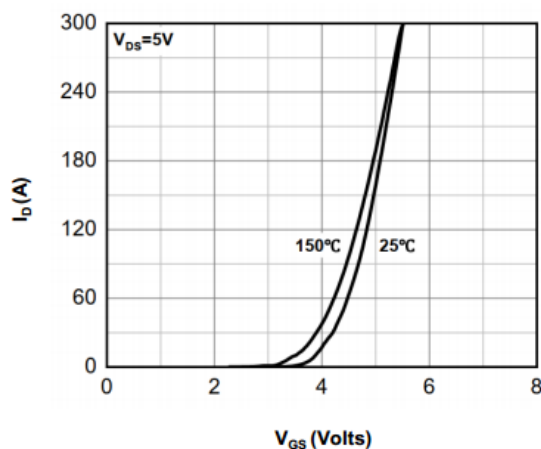


Figure 2: Transfer Characteristics

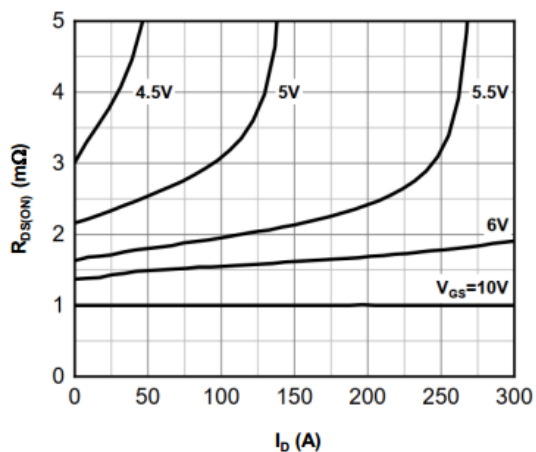


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

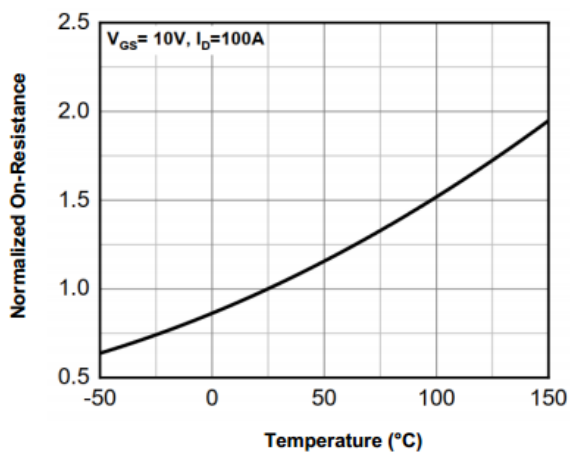


Figure 4: On-Resistance vs. Junction Temperature

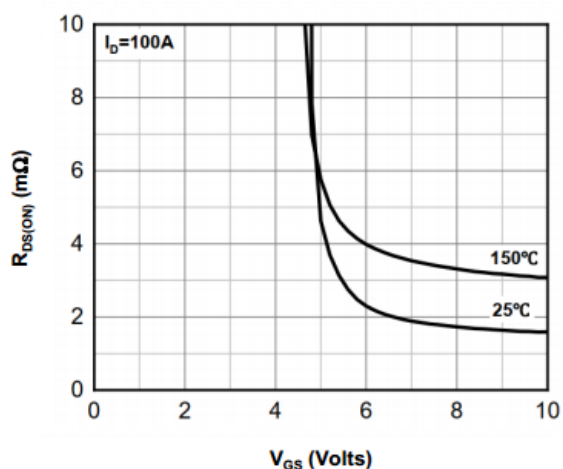


Figure 5: On-Resistance vs. Gate-Source Voltage

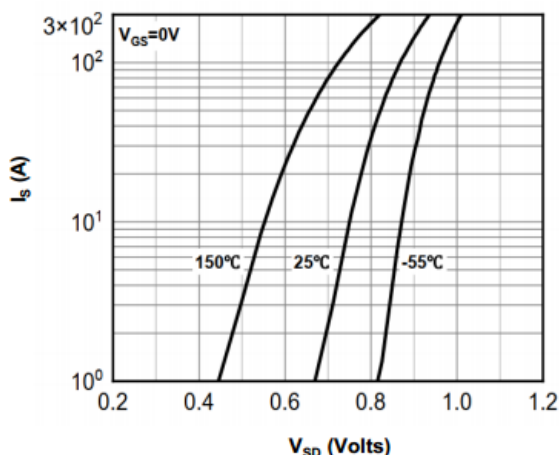
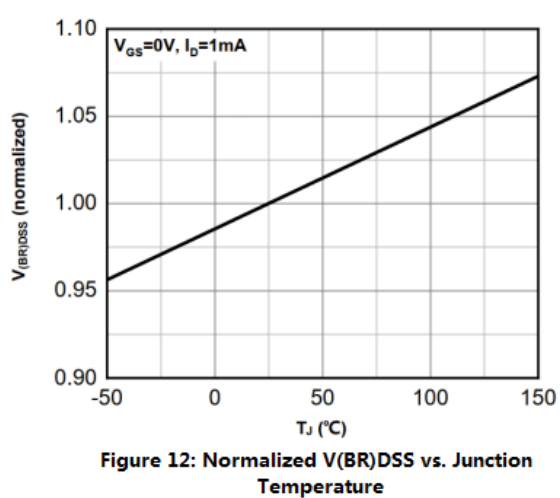
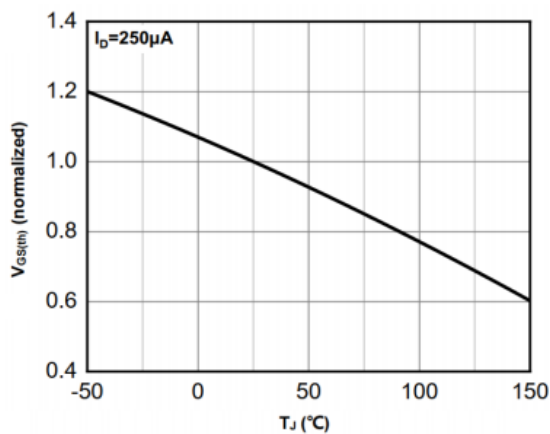
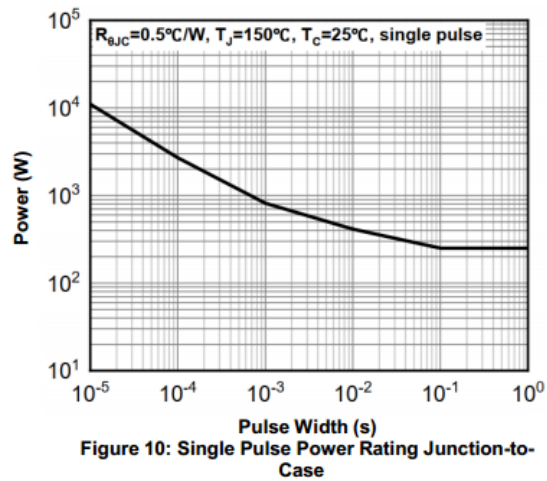
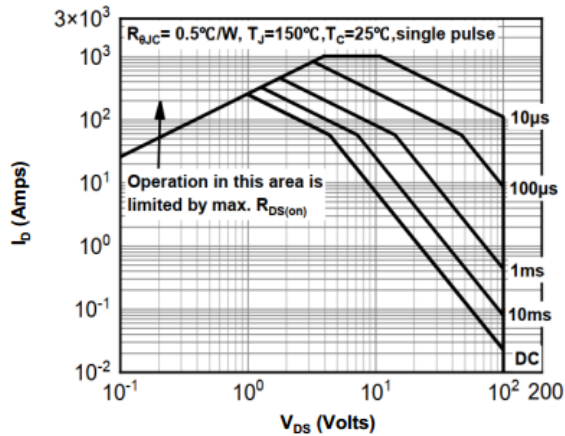
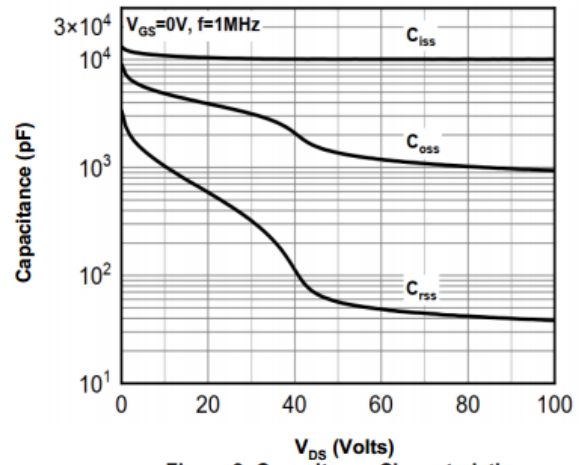
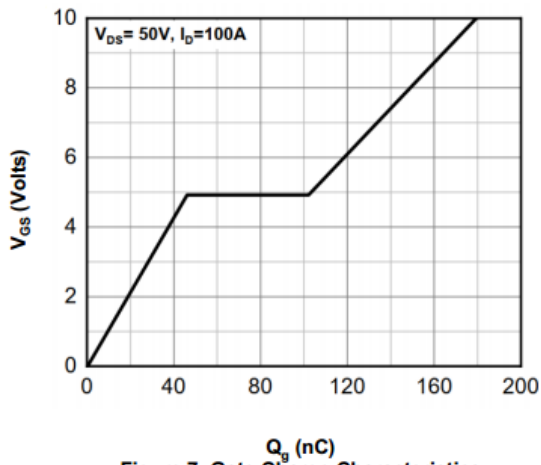
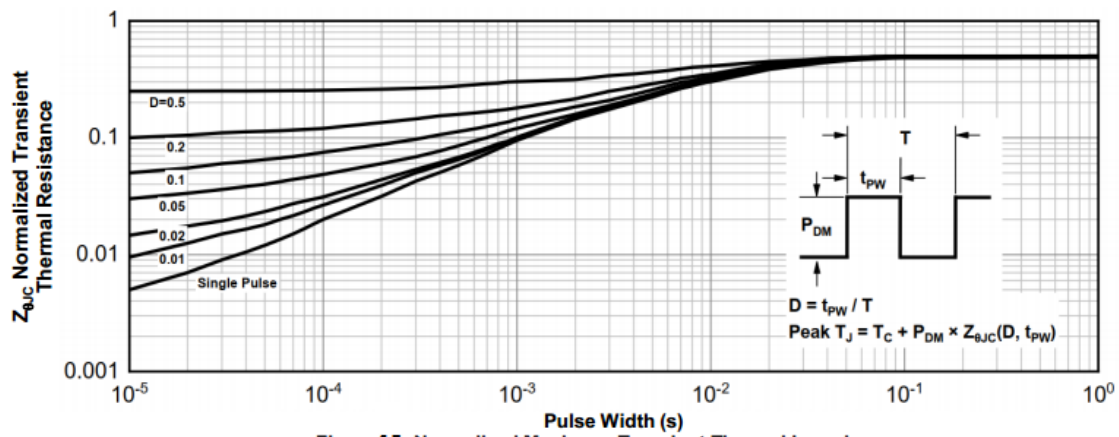
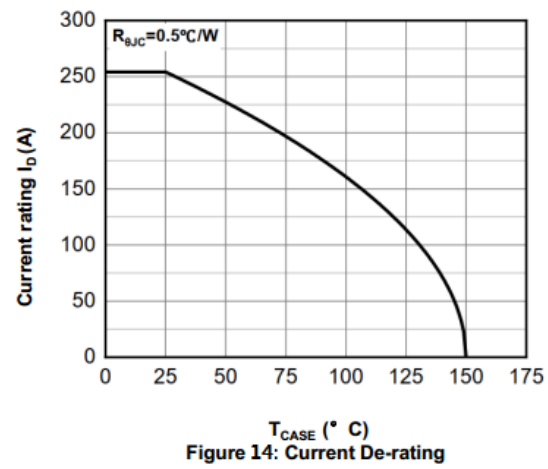
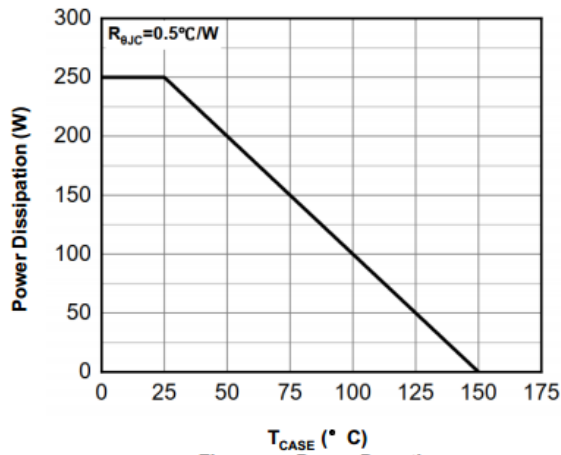


Figure 6: Body-Diode Characteristics

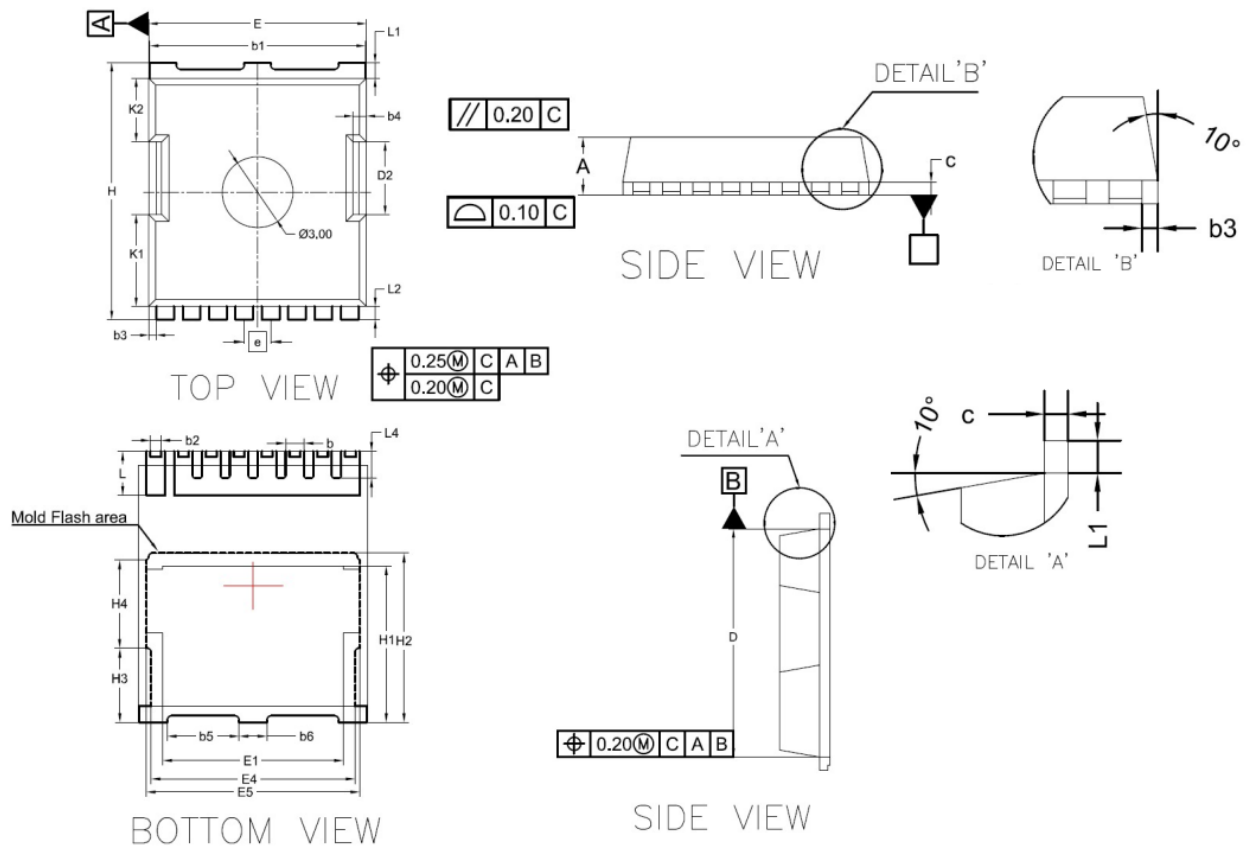
电参数曲线图 / Electrical Characteristic Curve



电参数曲线图 / Electrical Characteristic Curve



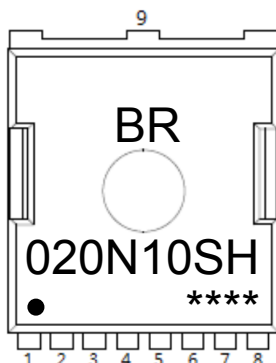
外形尺寸图 / Package Dimensions



Symbol	Dimensions In Millimeters			Symbol	Dimensions In Millimeters		
	MIN.	NOM.	MAX.		MIN.	NOM.	MAX.
A	2.200	2.300	2.400	b1	9.700	9.800	9.900
c	0.492	0.500	0.508	b1	0.420	0.460	0.500
D	10.280	10.380	10.480	b3	0.350		
E	9.800	9.900	10.000	b4	0.600		
e	1.20 BSC			b5	3.100		
H	11.580	11.680	11.780	b6	1.200		
H1	6.650	6.750	6.850	L	1.700	1.900	2.100
H2	7.300			L1	0.700		
H3	3.200			L2	0.600		
H4	3.800			L4	1.050	1.150	1.250
K1	4.180			L5	0.500	0.600	0.700
K2	2.900			E1	7.800		
D2	3.300			E4	8.800		
b	0.700	0.800	0.900	E5	9.200		



印章说明 / Marking Instructions



说明：

BR： 为公司代码

020N10SH： 为型号代码

****： 为生产批号代码，随生产批号变化

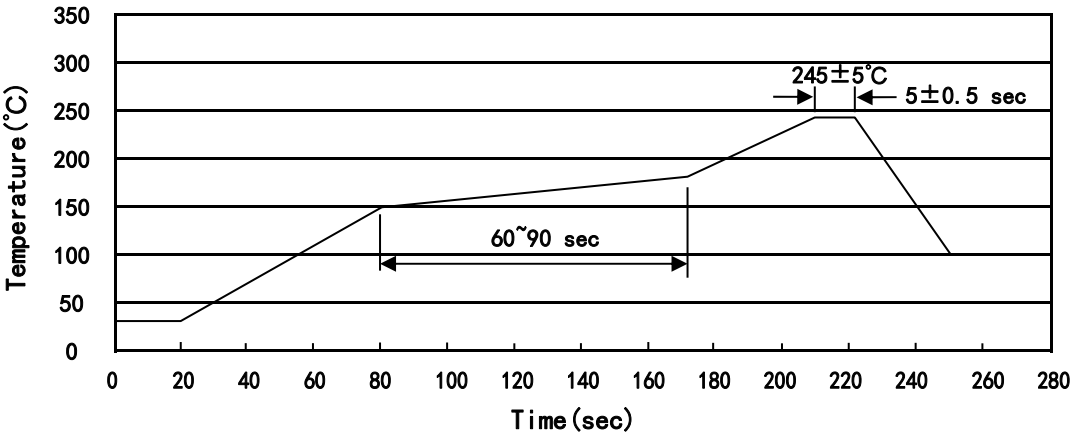
Note：

BR： Company Code

020N10SH： Product Type Code

****: Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180°C，时间 60~90sec；
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec；
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C 时间：10±1 sec. Temp.:260±5°C Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TOLL-8L	2,000	1	2,000	6	12,000	13"×24	360×360×50	380×335×366

使用说明 / Notices

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